

# Kyung Jean Yoon

## List of Publications by Citations

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The third column is the impact factor (IF) of the journal, and the fourth column is the number of citations of the article.

36 papers	1,613 citations	20 h-index	38 g-index
38 ext. papers	1,787 ext. citations	8.4 avg, IF	4.4 L-index

#	Paper	IF	Citations
36	A Review of Three-Dimensional Resistive Switching Cross-Bar Array Memories from the Integration and Materials Property Points of View. <i>Advanced Functional Materials</i> , <b>2014</b> , 24, 5316-5339	15.6	259
35	Highly Uniform, Electroforming-Free, and Self-Rectifying Resistive Memory in the Pt/Ta <sub>2</sub> O <sub>5</sub> /HfO <sub>2</sub> -x/TiN Structure. <i>Advanced Functional Materials</i> , <b>2014</b> , 24, 5086-5095	15.6	157
34	Highly improved uniformity in the resistive switching parameters of TiO <sub>2</sub> thin films by inserting Ru nanodots. <i>Advanced Materials</i> , <b>2013</b> , 25, 1987-92	24	152
33	32 B <sub>2</sub> Crossbar Array Resistive Memory Composed of a Stacked Schottky Diode and Unipolar Resistive Memory. <i>Advanced Functional Materials</i> , <b>2013</b> , 23, 1440-1449	15.6	136
32	Pt/Ta <sub>2</sub> O <sub>5</sub> /HfO <sub>2</sub> -x/Ti resistive switching memory competing with multilevel NAND flash. <i>Advanced Materials</i> , <b>2015</b> , 27, 3811-6	24	134
31	Nociceptive Memristor. <i>Advanced Materials</i> , <b>2018</b> , 30, 1704320	24	69
30	Electronic resistance switching in the Al/TiO(x)/Al structure for forming-free and area-scalable memory. <i>Nanoscale</i> , <b>2015</b> , 7, 11063-74	7.7	63
29	Memristive tri-stable resistive switching at ruptured conducting filaments of a Pt/TiO <sub>2</sub> /Pt cell. <i>Nanotechnology</i> , <b>2012</b> , 23, 185202	3.4	62
28	Improved endurance of resistive switching TiO <sub>2</sub> thin film by hourglass shaped Magn <sub>2</sub> filaments. <i>Applied Physics Letters</i> , <b>2011</b> , 98, 262901	3.4	60
27	Titanium dioxide thin films for next-generation memory devices. <i>Journal of Materials Research</i> , <b>2013</b> , 28, 313-325	2.5	56
26	What Will Come After V-NAND? Vertical Resistive Switching Memory?. <i>Advanced Electronic Materials</i> , <b>2019</b> , 5, 1800914	6.4	38
25	Double-Layer-Stacked One Diode-One Resistive Switching Memory Crossbar Array with an Extremely High Rectification Ratio of 10 <sup>9</sup> . <i>Advanced Electronic Materials</i> , <b>2017</b> , 3, 1700152	6.4	35
24	Evolution of the shape of the conducting channel in complementary resistive switching transition metal oxides. <i>Nanoscale</i> , <b>2014</b> , 6, 2161-9	7.7	34
23	Substrate Dependent Growth Behaviors of Plasma-Enhanced Atomic Layer Deposited Nickel Oxide Films for Resistive Switching Application. <i>Chemistry of Materials</i> , <b>2012</b> , 24, 4675-4685	9.6	33
22	Fabrication of a Cu-Cone-Shaped Cation Source Inserted Conductive Bridge Random Access Memory and Its Improved Switching Reliability. <i>Advanced Functional Materials</i> , <b>2019</b> , 29, 1806278	15.6	33
21	Comprehensive Writing Margin Analysis and its Application to Stacked one Diode-One Memory Device for High-Density Crossbar Resistance Switching Random Access Memory. <i>Advanced Electronic Materials</i> , <b>2016</b> , 2, 1600326	6.4	31
20	Schottky diode with excellent performance for large integration density of crossbar resistive memory. <i>Applied Physics Letters</i> , <b>2012</b> , 100, 213508	3.4	30

19	Fully Functional Logic-In-Memory Operations Based on a Reconfigurable Finite-State Machine Using a Single Memristor. <i>Advanced Electronic Materials</i> , <b>2018</b> , 4, 1800189	6.4	26
18	Uniform Self-rectifying Resistive Switching Behavior via Preformed Conducting Paths in a Vertical-type Ta <sub>2</sub> O <sub>5</sub> /HfO <sub>2</sub> -x Structure with a Sub-10 <sup>2</sup> Cell Area. <i>ACS Applied Materials &amp; Interfaces</i> , <b>2016</b> , 8, 18215-21	9.5	24
17	Filament Shape Dependent Reset Behavior Governed by the Interplay between the Electric Field and Thermal Effects in the Pt/TiO <sub>2</sub> /Cu Electrochemical Metallization Device. <i>Advanced Electronic Materials</i> , <b>2017</b> , 3, 1600404	6.4	20
16	A crossbar resistance switching memory readout scheme with sneak current cancellation based on a two-port current-mode sensing. <i>Nanotechnology</i> , <b>2016</b> , 27, 485201	3.4	19
15	A Stateful Logic Family Based on a New Logic Primitive Circuit Composed of Two Antiparallel Bipolar Memristors. <i>Advanced Intelligent Systems</i> , <b>2020</b> , 2, 1900082	6	19
14	A study of the transition between the non-polar and bipolar resistance switching mechanisms in the TiN/TiO <sub>2</sub> /Al memory. <i>Nanoscale</i> , <b>2016</b> , 8, 16455-66	7.7	18
13	Ionic bipolar resistive switching modes determined by the preceding unipolar resistive switching reset behavior in Pt/TiO <sub>2</sub> /Pt. <i>Nanotechnology</i> , <b>2013</b> , 24, 145201	3.4	18
12	Single-Cell Stateful Logic Using a Dual-Bit Memristor. <i>Physica Status Solidi - Rapid Research Letters</i> , <b>2019</b> , 13, 1800629	2.5	17
11	Resistance switching behavior of atomic layer deposited SrTiO <sub>3</sub> film through possible formation of Sr <sub>2</sub> Ti <sub>6</sub> O <sub>13</sub> or Sr <sub>1</sub> Ti <sub>11</sub> O <sub>20</sub> phases. <i>Scientific Reports</i> , <b>2016</b> , 6, 20550	4.9	16
10	Comparison of the Atomic Layer Deposition of Tantalum Oxide Thin Films Using Ta(NBu)(NEt), Ta(NBu)(NEt)Cp, and HO. <i>ACS Applied Materials &amp; Interfaces</i> , <b>2017</b> , 9, 537-547	9.5	13
9	Interface engineering for improving reliability of resistance switching in Cu/HfO <sub>2</sub> /TiO <sub>2</sub> /Pt structure. <i>Applied Physics Letters</i> , <b>2015</b> , 107, 072901	3.4	12
8	Optimization of chemical structure of Schottky-type selection diode for crossbar resistive memory. <i>ACS Applied Materials &amp; Interfaces</i> , <b>2012</b> , 4, 5338-45	9.5	9
7	In-Memory Stateful Logic Computing Using Memristors: Gate, Calculation, and Application. <i>Physica Status Solidi - Rapid Research Letters</i> , <b>2021</b> , 15, 2100208	2.5	8
6	Control of conducting filaments in TiO <sub>2</sub> films by a thin interfacial conducting oxide layer at the cathode. <i>Applied Physics Letters</i> , <b>2013</b> , 102, 082903	3.4	7
5	Resistive Memory: 32 B2 Crossbar Array Resistive Memory Composed of a Stacked Schottky Diode and Unipolar Resistive Memory (Adv. Funct. Mater. 11/2013). <i>Advanced Functional Materials</i> , <b>2013</b> , 23, 1350-1350	15.6	2
4	Weight Update Generation Circuit Utilizing Phase Noise of Integrated Complementary Metal-Oxide-Semiconductor Ring Oscillator for Memristor Crossbar Array Neural Network-Based Stochastic Learning. <i>Advanced Intelligent Systems</i> , <b>2020</b> , 2, 2000011	6	1
3	Next-Generation Memory: Double-Layer-Stacked One Diode-One Resistive Switching Memory Crossbar Array with an Extremely High Rectification Ratio of 10 <sup>9</sup> (Adv. Electron. Mater. 7/2017). <i>Advanced Electronic Materials</i> , <b>2017</b> , 3,	6.4	1
2	In-Memory Hamming Error-Correcting Code in Memristor Crossbar. <i>IEEE Transactions on Electron Devices</i> , <b>2022</b> , 1-8	2.9	1

1 Poster: Memristive Systems523-587